

# RAA23022x RAA23023x [Under Development]

16V Input, 3A, Dual Step-Down DC/DC Converter

+ Battery Backup

R18DS0017EJ0000 REV.0.00 Aug.19.2014

## Description

The RAA23022x and RAA23023x are dual step-down DC/DC converter, 4.5V to 16V input voltage rage and 3A output current. Auto PFM mode makes devices low power operation at light load, so it makes a system lower power.

The RAA23022x is suitable for battery backup system using lithium primary cell with built-in battery backup circuit.

## Features

• DC/DC	
Input voltage range	4.5V to 16V
Shutdown current	luA (typ.)
Auto PFM mode	
Maximum output current	3A
Synchronous rectification type step-down DC	/DC
Integrated power MOSFETs	
Switching frequency	1.1MHz (fixed)
Output voltage range	0.8V to 6V
Internal phase compensator	
Soft start	2ms (fixed)
Discharge circuit	
Power Good	
Battery backup circuit (RAA23022x)	
• Protection circuit	
Short circuit protection (latch type)	
Thermal shutdown circuit	165°C (typ.)
Under voltage lockout circuit (recovery type)	
• Package	
20-pin HTSSOP	

## Application

Communication (Router, Home Gate Way, Radio, etc.) Industrial (Surveillance camera, Various controller, etc.) Building (Security device, Emergency device, Various controller, etc.) OA (Printer, Plane paper copier, etc.) Smart meter Smart home appliances And, usable various application

Note: The information contained in this document is being issued in advance of the production cycle for the product. The parameters for the product may change before final production, or Renesas Electronics Corporation, at its own discretion, may withdraw the product prior to its production.

A quality grade of these ICs is "Standard". Recommended applications are indicated below. Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment, and industrial robots, etc.



# Product Lineup Table

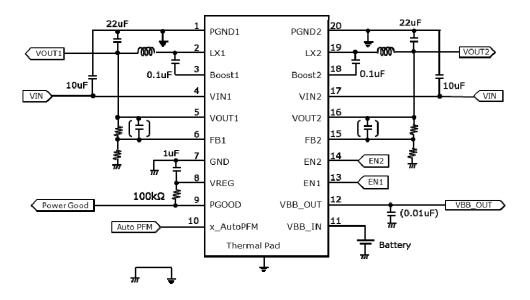
Part number	Output	Туре	VIN range	VOUT	IOUT (max.)	Switching frequency
RAA230221	2	Step-down + BB	4.5 to 16V	CH1 3.3V (fixed) CH2 0.8V to 6.0V* <sup>1</sup>	3A	1.1MHz
RAA230222	2	Step-down + BB	4.5 to 16V	CH1 3.3V (fixed) CH2 5.0V (fixed)	3A	1.1MHz
RAA230223	2	Step-down + BB	4.5 to 16V	CH1 and CH2 0.8V to 6.0V* <sup>1</sup>	3A	1.1MHz
RAA230231	2	Step-down	4.5 to 16V	CH1 3.3V (fixed) CH2 0.8V to 6.0V* <sup>1</sup>	3A	1.1MHz
RAA230232	2	Step-down	4.5 to 16V	CH1 3.3V (fixed) CH2 5.0V (fixed)	3A	1.1MHz
RAA230233	2	Step-down	4.5 to 16V	CH1 and CH2 0.8V to 6.0V* <sup>1</sup>	3A	1.1MHz

Note BB : Battery Backup

\*1 Set by external resistors

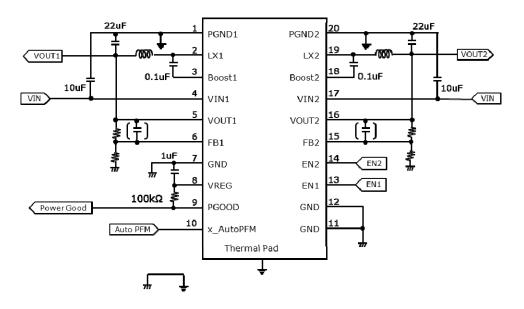


## **Circuit example**



RAA23022x (2CH DCDC + Battery Backup, VOUT set by external resistors)

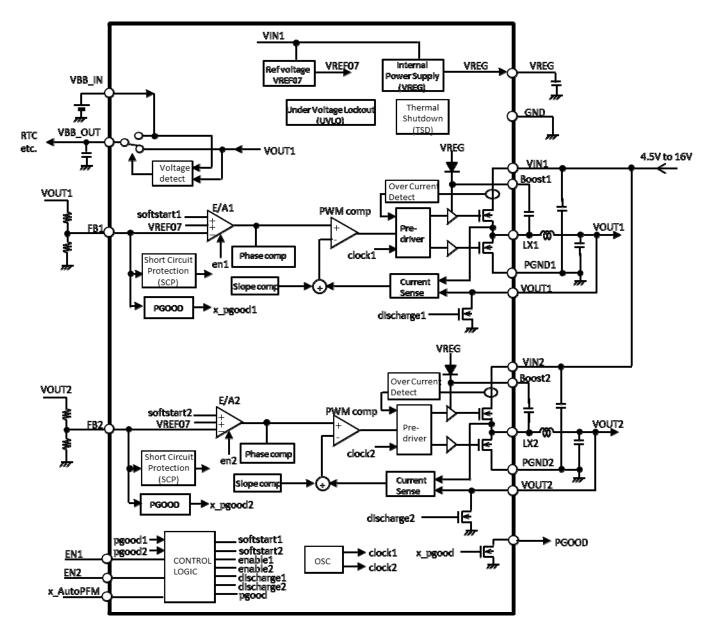
#### RAA23023x (2CH DCDC, VOUT set by external resistors)





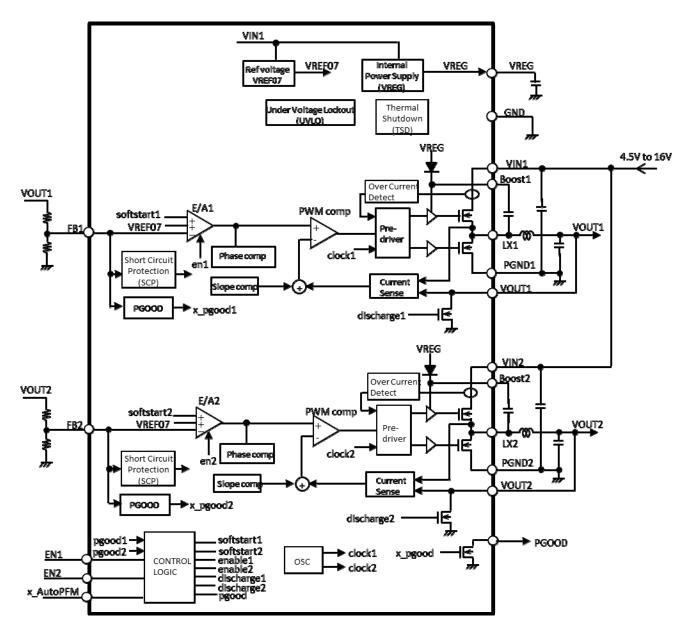
## **Block Diagram**

RAA23022x (2CH DCDC + Battery backup, VOUT set by external resistors)











## **Pin Function**

## RAA23022x (2CH DCDC + Battery backup)

Pin No.	Symbol	I/O	Function	
1	PGND1	I/O	CH1 Power Ground	
2	LX1	0	CH1 Inductor connection	
3	Boost1	I	CH1 Boot strap input	
3			(Connect 0.1uF capacitor between LX1 and Boost1)	
4	VIN1	I	CH1 Power supply	
5	VOUT1	I	CH1 VOUT feedback	
6	FB1	I	CH1 Feedback resistor connection	
7	GND	I/O	Analog Ground	
0			Internal power supply output	
8	VREG	0	(Connect 1uF capacitor between VREG and AGND)	
			Power good output (open drain)	
9	PGOOD	0	CH1 and CH2 stop :L	
			CH1 or CH2 operation : HiZ	
			Auto PFM mode ON/OFF	
			x_AutoPFM="L" : Auto PFM mode (change automatically)	
10	x_AutoPFM	I	PFM mode at light load	
			PWM mode at heavy load	
			x_AutoPFM="H" : PWM mode (fixed)	
11	VBB_IN	I	Battery connection	
12	VBB_OUT	0	Backup voltage output	
			CH1 enable	
13	EN1	I	EN1="L" or open : CH1 Stop	
			EN1="H" : CH1 Operation	
			CH2 enable	
14	EN2	I	EN2="L" or open : CH2 Stop	
			EN2="H" : CH2 Operation	
15	FB2	I	CH2 Feedback resistor connection	
16	VOUT2	I	CH2 VOUT feedback	
17	VIN2	I	CH2 Power supply	
18	Boost2	I	CH2 Boot strap input	
10			(Connect 0.1uF capacitor between LX2 and Boost2)	
19	LX2	0	CH2 Inductor connection	
20	PGND2	I/O	CH2 Power Ground	



## RAA23023x (2CH DCDC)

Pin No.	Symbol	I/O	Function	
1	PGND1	I/O	CH1 Power Ground	
2	LX1	0	CH1 Inductor connection	
2	Boost1	I	CH1 Boot strap input	
3			(Connect 0.1uF capacitor between LX1 and Boost1)	
4	VIN1	I	CH1 Power supply	
5	VOUT1	I	CH1 VOUT feedback	
6	FB1	I	CH1 Feedback resistor connection	
7	GND	I/O	Analog Ground	
0		_	Internal power supply output	
8	VREG	0	(Connect 1uF capacitor between VREG and AGND)	
			Power good output (open drain)	
9	PGOOD	0	CH1 and CH2 stop :L	
			CH1 or CH2 operation : HiZ	
			Auto PFM mode ON/OFF	
			x AutoPFM="L" : Auto PFM mode (change automatically)	
10	x_AutoPFM	I	PFM mode at light load	
			PWM mode at heavy load	
			x_AutoPFM="H" : PWM mode (fixed)	
11	GND	I/O	Analog Ground	
12	GND	I/O	Analog Ground	
			CH1 enable	
13	EN1	I	EN1="L" or open : CH1 Stop	
			EN1="H" : CH1 Operation	
			CH2 enable	
14	EN2	I	EN2="L" or open : CH2 Stop	
			EN2="H" : CH2 Operation	
15	FB2	I	CH2 Feedback resistor connection	
16	VOUT2	I	CH2 VOUT feedback	
17	VIN2	I	CH2 Power supply	
18	Boost2	I	CH2 Boot strap input	
10			(Connect 0.1uF capacitor between LX2 and Boost2)	
19	LX2	0	CH2 Inductor connection	
20	PGND2	I/O	CH2 Power Ground	



## **Absolute Maximum Ratings**

		(Unle	ss otherwis	e specified, $TA = 25^{\circ}C$ ,)
Parameter	Symbol	Ratings	Unit	Condition
VIN applied voltage	VIN	-0.3 to +17.6	V	VIN1, VIN2
EN applied voltage	EN	-0.3 to +17.6	V	EN1, EN2
x_AutoPFM applied voltage	x_AutoPFM	-0.3 to +17.6	V	x_AutoPFM
PGOOD voltage	PGOOD	T.B.D.	V	PGOOD
FB applied voltage	FB	-0.3 to +6.5	V	FB1, FB2
VOUT applied voltage	VOUT	-0.3 to +6.5	V	VOUT1, VOUT2
VBB_IN applied voltage (RAA23022x)	VBB_IN	-0.3 to +6.5	V	VBB_IN
VIN input current(peak)	IVIN(peak)-	4.2	А	VIN1, VIN2
LX output current(peak)	ILX(peak)+	4.2	А	LX1, LX2
VOUT sink current (DC)	IVOUT(DC)-	(100)	mA	VOUT1, VOUT2 When discharge circuit operation
GND voltage	GND	-0.3 to +0.3	V	PGND1, PGND2, GND
Total power dissipation	PT	T.B.D. <sup>*1</sup>	mW	TA≦+25°C
Operating ambient temperature	TA	-40 to (+85)	°C	
Operation junction temperature	TJ	-40 to (+125)	°C	
Storage temperature Note: T.B.D. :To be determined.	Tstg	-55 to +150	°C	

\*1 This is the value at  $T_A < +25^{\circ}$ C. At  $T_A > +25^{\circ}$ C, the total power dissipation decrease with -T.B.D. mW/°C.

Caution: Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

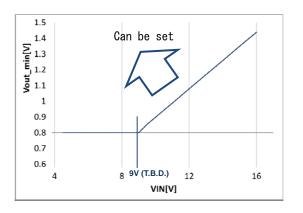


## **Recommended Operating Condition**

Symbol	MIN.	TYP.	MAX.	Unit	Condition
VIN	4.5		16.0	V	VIN1, VIN2
EN	0		16.0	V	EN1, EN2
x_AutoPFM	0		16.0	V	x_AutoPFM
PGOOD	0		T.B.D.	V	PGOOD
FB	0		6.0	V	FB1, FB2
Vdcdc_ext	See diagram below		6.0	V	At external resistor setting
	VIN EN x_AutoPFM PGOOD FB	VIN4.5EN0x_AutoPFM0PGOOD0FB0Vdcdc_extSee diagram	VIN4.5EN0x_AutoPFM0PGOOD0FB0Vdcdc_extSee diagram	VIN         4.5         16.0           EN         0         16.0           x_AutoPFM         0         16.0           PGOOD         0         T.B.D.           FB         0         6.0           Vdcdc_ext         diagram         6.0	VIN         4.5         16.0         V           EN         0         16.0         V           x_AutoPFM         0         16.0         V           PGOOD         0         T.B.D.         V           FB         0         6.0         V           Vdcdc_ext         diagram         6.0         V

Note: T.B.D. : To be determined.

Minimum value of VOUT setting range (T.B.D.)





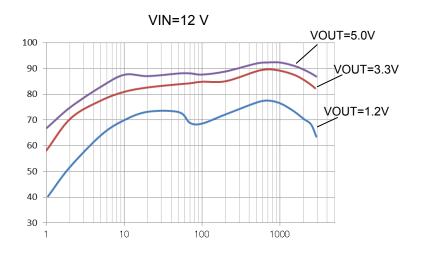
	Parameter	Symbol	MIN.	TYP.	MAX.	Unit	Condition
Tatal		-					EN1 = EN2 = GND
Total	Shutdown current	IDD(SHDN)		1	10	uA	-
Under voltage lock	Operating start voltage	Vdet(vin)	3.5	3.8	4.1	V	VIN1 and VIN2 rising are detected
out circuit (UVLO)	VIN hysteresis	Vhys(vin)	0.24	0.30	0.36	V	VIN1 and VIN2 falling are detected
Internal power supply (VREG)	Internal power supply voltage	VREG	4.7	5.0	5.3	V	Ireg = 0mA, VIN1 = 6V to 16V
	E/A feedback voltage	vref07	(0.693)	0.700	(0.707)	V	Include input offset at external resistor setting
Output	Output voltage accuracy	Vacc	(-2.5)		(+2.5)	%	Fixed VOUT products
(PWM mode)	High side FET on-resistance	Ronh		100		mΩ	VIN1, VIN2 = 6V to 16V
	Low side FET on-resistance	Ronl		70		mΩ	VIN1, VIN2 = 6V to 16V
Discharge circuit	On-resistance	Rondc		(100)	(200)	Ω	CH1, CH2
Soft start	Soft start time	tss		2		ms	
Thermal	Detect temperature <sup>*1</sup>			165		°C	
shutdown circuit	Hysteresis temperature <sup>*1</sup>			20		°C	
	High level threshold voltage	VIH	1.3		VIN+0.3	V	EN1, EN2, x_AutoPFM
Logic input	Low level threshold voltage	VIL	-0.3		0.4	V	EN1, EN2, x_AutoPFM
0 1	Input current	IEN		1		uA	EN1 = 3.3V, EN2 = 3.3V x_AutoPFM = 3.3V
	VBB_IN input voltage range	VBB	2.7	3.0	3.7	V	
Battery backup (RAA23022x)	On-resistance between VBB_IN and VBB_OUT	Ron_vbat		400		Ω	VBB_OUT = VBB_IN
	On-resistance between VOUT1 and VBB_OUT	Ron_vout1		(90)		Ω	VBB_OUT = VOUT1
	(VBB leak current)	IL_BB		T.B.D.		uA	VBB_OUT = VBB_IN = 3.0V

T.B.D. :To be determined. \*1 Not production tested. Note:



# **Typical Performance Characteristics**

Efficiency vs. Output Current



(Unless otherwise specified,  $T_A = 25^{\circ}C$ )



## **Detailed Description**

### **Control Block**

EN1, EN2 : ON/OFF setting

EN1	EN2	State	VREG
L	L	Shutdown	0V
		(CH1 and CH2 stop)	
Н	L	CH1 Operation	5.0V
п		CH2 Stop	
Н	Н	CH1 and CH2 Operation	5.0V
	Н	Ch1 Stop	5.0V
L		CH2 Operation	

Note: L: Low level, H: High level

#### x\_autoPFM : AutoPFM mode/ PWM mode setting

x_autoPFM	Operation				
L	Auto PFM mode (change automatically)				
	PFM mode at light load				
	PWM mode at heavy load				
Н	PWM mode (fixed)				

Note: L: Low level, H: High level

#### PGOOD : Power Good output

State	PGOOD
CH1 and CH2 stop	L
CH1 or CH2 operation	HiZ

Note: L: Low level, H: High level

When VREG voltage falls under T.B.D. V, PGOOD pin becomes high impedance though CH1 and CH2 are Low.

When using this function, connect PGOOD pin to VREG, VOUT1, VOUT2, etc.



#### Auto PFM mode

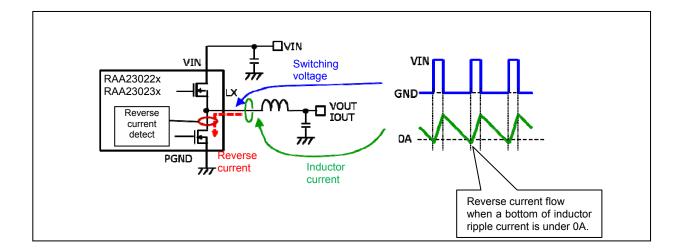
RAA23022x and RAA23023x have Auto PFM mode to achieve high efficiency over a wide load current range. The devices operate with PFM (Pulse Frequency Modulation) mode at light load current, and PWM (Pulse Width Modulation) mode at heavy load current. An operation mode is automatically switched depending on load current.

When a bottom of inductor ripple current is under 0A, reverse current flow at low-side N-channel MOSFET of output block. The devices operate with PFM mode during detecting this current. A current of switching PFM / PWM mode (I<sub>change</sub>) is calculated by an equation below.

A current of switching PFM / PWM mode (I<sub>change</sub>) is calculated by an equation belo  $I_{change} = \frac{\Delta IL}{2}$ 

$$-\frac{1}{2}$$

$$\Delta IL = \frac{(V_{IN} - V_{OUT})}{L} \times \frac{V_{OUT}}{V_{IN}} \times \frac{1}{f_{SW}}$$



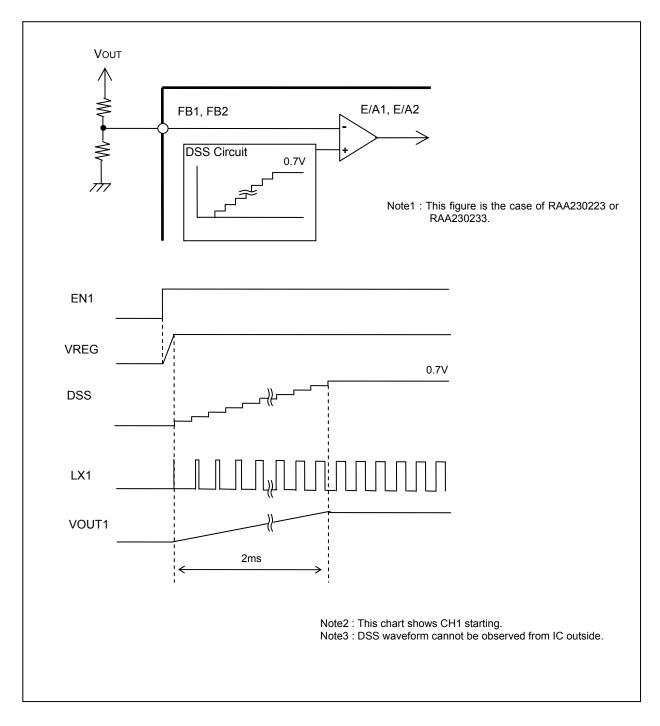
L: inductance, f<sub>SW</sub>: 1.1MHz

RAA23022x and RAA23023x have x\_autoPFM pin. When Low level, the devices operate Auto PFM mode (PFM mode / PWM mode changed automatically). When High level, the devices operate PWM mode, then not change into Auto PFM mode.



#### Soft Start

To limit the startup inrush current and output voltage overshoot, a soft start circuit is used to ramp up the reference voltage from 0 V to its final value linearly. When EN pin is set from low level to high level, the device starts operation and output voltage rises with soft start. Both CH1 and CH2 soft start time are fixed at 2ms(Typ.) and no additional components are needed. Soft start feature gradually increases the error amplifier (E/A) input threshold voltage by using the voltage that is generated by the digital soft start (DSS) circuit.





#### **Discharge Circuit**

The device has discharge circuit in both CH1 and CH2. This enables a rapid discharge without an external MOSFET. When an EN pin is changed from high level to low, each discharge switch in VOUT pin is turned on and all capacitors which are connected to each output are rapidly discharged through VOUT pin.

When VIN pin voltage becomes low level, discharge switches become off because there are no voltage to keep them on. The control voltage of discharge switches is VREG, and the discharge time of VREG capacitor is over 100ms when VIN voltage falls down, so even if EN pin is connected to VIN pin, an output voltage can be discharged because VREG voltage level can keep the discharge switches on. When VREG voltage falls, VOUT pin becomes high impedance.

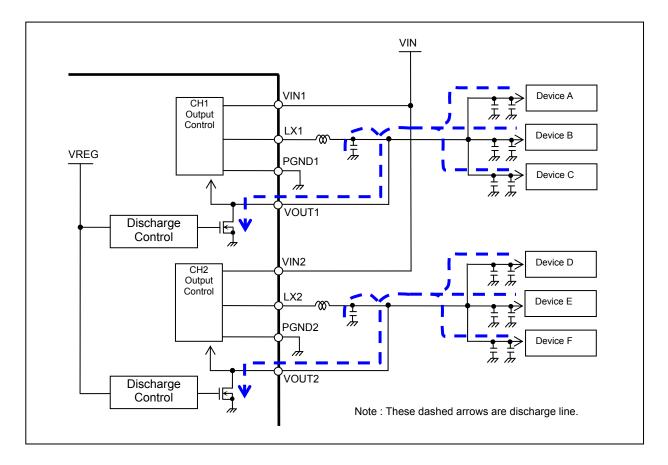
Discharge time can be calculated by an equation below.

$$V_{dc} = V_{OUT} \times e^{-\frac{t_{dc}}{C_{ALL} \times R_{ondc}}}$$

 $V_{dc}$  is a voltage after  $t_{dc}(s)$ .

 $C_{ALL}$  is sum of all capacitance which are connected to CH1 or CH2 output (output capacitor, bypass capacitor around MCU, etc.).

 $R_{\text{ondc}}$  is on resistance of discharge circuit.

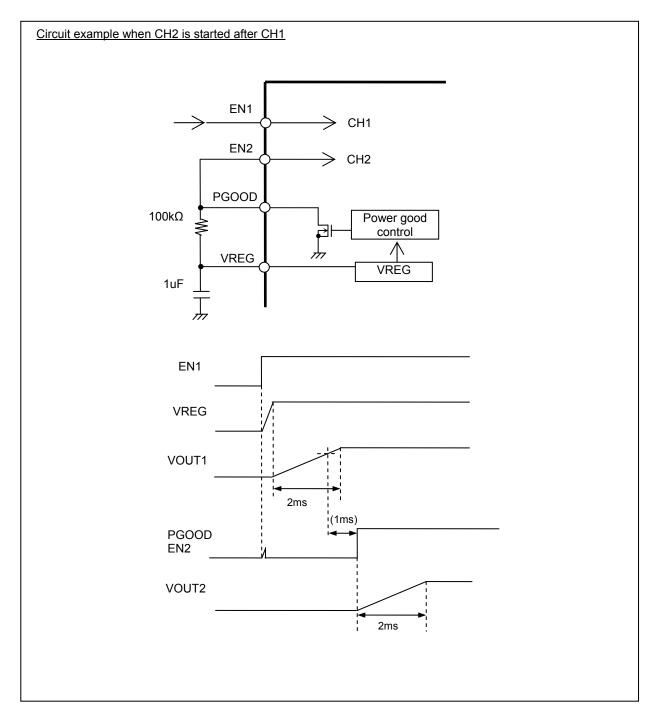




#### **Power Good**

Power Good is an open-drain output that requires a pull – up resistor (Recommended value =  $100k\Omega$ ). PGOOD pin becomes high impedance (HiZ) when either CH1 or CH2 FB pin voltage and thus its output voltage rises above T.B.D.% of nominal regulation point. If it is pulled-up, PGOOD output high level. PGOOD pin goes low when both CH1 or CH2 output voltage falls below T.B.D.% of the regulation point. When both EN1 and EN2 pin goes low level, PGOOD pin becomes HiZ because VREG is used for power good control and it fall down at this time. So, if PGOOD pin is connected to VIN, its status becomes high level even if CH1 and CH2 stop. PGOOD pin must be pulled up to CH1 output, CH2 output or VREG when using this function.

CH1 and CH2 can be started in order by connecting PGOOD pin to EN1 or EN2. This function can be also used for sequence signal for other devices.





#### Battery Backup (RAA23022x)

RAA23022x has a battery backup circuit which is used to operate some devices at system power-off. The circuit can be easily designed by RAA23022x without two diodes.

When CH1 operates, VBB\_OUT = VOUT1. When CH1 stops and VOUT1 pin voltage is higher than VBB\_IN pin, VBB\_OUT = VOUT1 pin. When CH1 stops and VOUT1 pin voltage is lower than VBB\_IN pin, VBB\_OUT = VBB\_IN pin.

VBB\_OUT voltage value is dependent on on-resistance between VBB\_IN and VBB\_OUT, On-resistance between VOUT1 and VBB\_OUT and VBB\_OUT output current. VBB\_OUT can be calculated by equations below.

1. Normal operation mode (VBB\_OUT = VOUT1)

$$V_{BB_{OUT}} = V_{OUT1} - I_{BB_{OUT}} \times R_{on\_vout1}$$

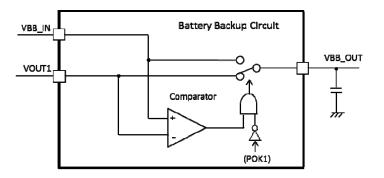
2. Battery backup mode (VBB\_OUT = VBB\_IN)

$$V_{BB_OUT} = V_{BB_IN} - I_{BB_OUT} \times R_{on\_vbat}$$

 $\begin{array}{l} V_{BB\_OUT}:VBB\_OUT \ voltage \ (V) \\ V_{OUT1}:VOUT1 \ voltage = CH1 \ output \ voltage \ (V) \\ V_{BB\_IN}:VBB\_IN \ voltage = Battery \ voltage \ (V) \\ I_{BB\_OUT}:VBB\_OUT \ output \ current \ (A) \\ R_{on\_vout1}: On \ resistance \ between \ VOUT1 \ and \ VBB\_OUT \ 90\Omega \ (Typ.) \\ R_{on\_vbat}:On \ resistance \ between \ VBB\_IN \ and \ VBB\_OUT \ 400\Omega \ (Typ.) \end{array}$ 

Note : T.B.D.  $(1.8V) \le V_{BB_OUT} \le 3.7V$ 

Connect T.B.D. nF capacitor to VBB\_OUT pin.



Note : POK1 is an IC internal signal which identifies CH1 operating status. It cannot be seen from IC outside. After CH1 has started up, there is about 1ms delay time till POK1 becomes high level.

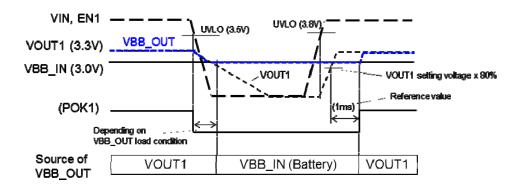
#### VBB\_OUT pin output status

CH1	VOUT1, VBB_IN	VBB_OUT
Operation	VOUT1 ≥ VBB_IN	VOUT1
(POK1 = H)	or	
	VOUT1 < VBB_IN	
Stop	VOUT1 ≥ VBB_IN	VOUT1
(POK1 = L)	VOUT1 < VBB_IN	VBB_IN

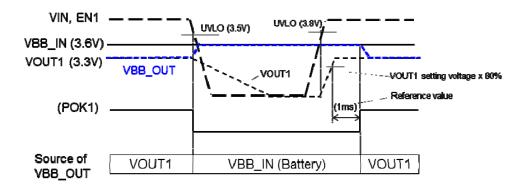
Note : L: Low level, H: High level

Timing chart of battery backup

1. With 3.0V battery



2. With 3.6V battery





Protection	Function	Operatior	status	Reset	
circuit		Common circuit (VREG, etc.)	CH1, CH2 Output		
Short circuit protection (SCP)	Detect output voltage dropping because of short circuit, etc. (Latch type)	Operation	Latched to off	Turn EN1 and EN2 pin from high level to low level or Drop VIN1 and VIN2 pin voltage under operation stop voltage of UVLO	
Thermal shutdown circuit (TSD)	Detect rise up of IC internal temperature (Over 165°C) (Auto recovery type)	Operation	Stop	The temperature falls	
Under voltage lockout circuit (UVLO)	Detect dropping of VIN (Auto recovery type)	Operation	Stop	Up VIN1 and VIN2 over operating start voltage (3.8V)	

Note SCP : Short Circuit Protection

TSD : Thermal Shutdown Circuit

UVLO : Under Voltage Lockout Circuit

#### Short Circuit Protection (Latch type)

When CH1 or CH2 output voltage drops, each FB pin input voltage also drops. If this voltage falls below the input detection voltage of the short circuit protection, the outputs both CH1 and CH2 are stopped (latched to OFF). At this time, common circuits (such as VREG, etc.) continue operating. When the protection is operating, to reset the latch, either turn the EN1 pin and EN2 pin from high to low or drop the VIN1 pin and VIN2 voltage under operation stop voltage of UVLO.



#### Thermal Shutdown Circuit (Auto Recovery Type)

When overheating has been detected (detect temperature:  $165^{\circ}$ C), the outputs both CH1 and CH2 is stopped. Then, power MOSFET of output both high side and low side are turned off. Common circuits (such as VREG, etc.) continue operating.

If the device temperature falls and becomes under detect temperature, the protection is canceled and output automatically resumes.

#### Under Voltage Lockout Circuit (Auto Recovery Type)

(1) Under voltage lockout operation

When the power supply voltage (VIN1 and VIN2) falls to the operation stop voltage (T.B.D.), output from all channels stops. Common circuits (such as VREG, etc.) continue operating.

(2) Restoring output

Once VIN1 and VIN2 is restored to the Operating start voltage (3.8V), the under voltage lockout operation is canceled and output automatically resumes. The output voltage cannot be restored while the under voltage lockout circuit is operating, not even by manipulating the EN pin.

#### **Current Limiting**

If an overcurrent occurs, an output current is limited on a pulse-by-pulse basis. If the current sensor detects an overcurrent, the current is limited and the switching operation of the Power MOSFET in the output stage stops until the next cycle.

When an output current is limited, the output voltage drops. If a FB pin voltage falls below the input detection voltage, the short-circuit protection circuit starts operating.

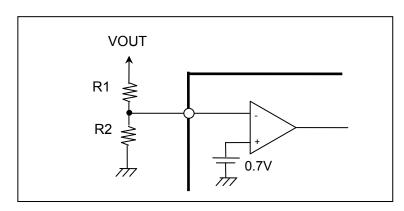


## **Guide for Circuit Design**

#### Setting Output Voltage (When the output voltage is set by external resistor)

The output voltage can be calculated by an equation below.

VOUT = 0.7 x (1 + R1 / R2)



#### Examples of R1 and R2 selection

Vout	0.9V	1.0V	1.05V	1.1V	1.18V	1.2V	1.5V	1.8V	2.5V	3.3V	5.0V
R1	180k	220k	180k	270k	270k	130k	150k	470k	620k	820k	680k
R2	620k	510k	360k	470k	390k	180k	130k	300k	240k	220k	110k

#### Output voltage accuracy (When the output voltage is set by external resistor)

Output voltage accuracy can be calculated by an equation below.

$$V_{OUTACC} = V_{ITHACC} + \frac{(Vout - V_{ITH})}{Vout} \times 2 \times R_{ACC}$$

 $V_{OUTACC}$  is the output voltage accuracy (%).

V<sub>ITHACC</sub> is the E/A input threshold voltage accuracy (%).

 $V_{OUT}$  is the output voltage (V).

 $R_{ACC}$  is the external resistor accuracy (%).

So, an output voltage accuracy of the device is below.

$$V_{OUTACC} = 1 + \frac{(Vout - 0.7)}{Vout} \times 2 \times R_{ACC}$$

Note : These equation don't include Vout fluctuation by load step transient.



#### Inductor selection

An inductor target is that ripple current ( $\Delta$ IL) of inductor becomes 10 to 40 % of Iout(max).

When  $\Delta IL$  increases, inductor current peak raises, so ripple of Vout gets larger and power loss increases. But, large size inductor is required to lower  $\Delta IL$ .

 $\Delta$ IL can be calculated by an equation below.

$$\Delta \text{IL} = \frac{(Vin - Vout)}{L} \times \frac{Vout}{Vin} \times \frac{1}{f_{SW}}$$

fsw is 1.1MHz.

Peak current of inductor (ILpeak) can be calculated by an equation below.

$$lL_{Peak} = l_{OUT}(MAX) + \frac{\Delta IL}{2}$$

Choose a inductor which saturation current is higher than ILpeak .

#### Inductor Example

Inductance (uH)	Inductor	Manufacturer	I <sub>TEMP</sub> (A)	I <sub>SAT</sub> (A)	Size (LxWxT, mm)
2.2	NRS5024T2R2NMGJ	TAIYO YUDEN	3.1	4.1	4.9x4.9x2.4
2.2	744778002	WURTH	4.0	4.8	7.3x7.3x3.2
3.3	NRS5030T3R3MMGJ	TAIYO YUDEN	3.0	3.6	4.9x4.9x3.1
3.3	7447789003	WURTH	3.4	4.2	7.3x7.3x3.2
4.7	NRS5040T4R7NMGK	TAIYO YUDEN	3.1	3.3	4.9x4.9x4.1
4.7	744777004	WURTH	4.0	4.0	7.3x7.3x4.3

Note I<sub>TEMP</sub> : Rated current by temperature rising

I<sub>SAT</sub> : Rated current by inductance loss

These inductors are examples. About inductor detail, contact each manufacturer



#### Output capacitor selection

RAA23022x and RAA23023x have a phase compensation circuit which is optimized to DC/DC operation. In order to operate stably with the phase compensation, connect the output capacitor which is over 22 uF. Ceramic capacitor can be used for output capacitor. It has low ESR, so VOUT ripple is decreased.

VOUT ripple ( $\Delta$ Vrpl) can be calculated by an equation below.

$$\Delta V_{rpl} = \Delta IL \times \left( ESR + \frac{1}{(8 \times C_{OUT} \times f_{SW})} \right)$$

ESR : Equivalent Series Resistance

#### Input capacitor selection

Connect an input capacitor which is over 10 uF between each VIN pin and power ground. It should be placed close to the device as possible.

#### **VREG** capacitor

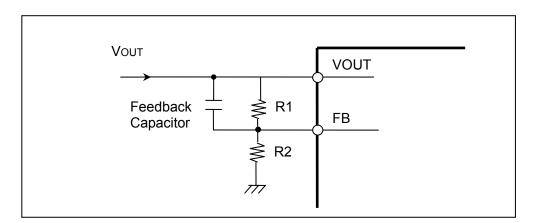
Connect 1uF ceramic capacitor to VREG pin.

#### Bootstrap capacitor

Connect 0.1uF ceramic capacitor between LX pin and Boost pin.

#### **Feedback capacitor**

When using Auto PFM mode, it is recommended to connect feedback capacitor in parallel to high side output voltage setting resistor to improve phase characteristic at Auto PFM mode.



#### **Components example**

	VIN (V)	VOUT (V)	L (uH)	Cout (uF)	C <sub>FB</sub> (pF)		
					Auto PFM mode	PWM mode	
		5V	3.3	22 to 44	47	-	
	12	3.3V	3.3	22 to 44	47	-	
		1.2V	3.3	22 to 44	T.B.D.	-	



## Notes on Use

#### **VIN Applied Voltage**

Be sure to apply the same voltage toVIN1 pin and VIN2 pin.

#### Pattern Wiring

To actually perform pattern wiring, separate a ground of control signal from a ground of a power line, so that these grounds do not have a common impedance as much as possible.

#### **Connection of Exposed PAD**

HTSSOP package has an Exposed PAD on the bottom to improve radiation performance. On the mounting board, connect this Exposed PAD to PGND or GND.

#### **Fixed Usage of Control Input Pin**

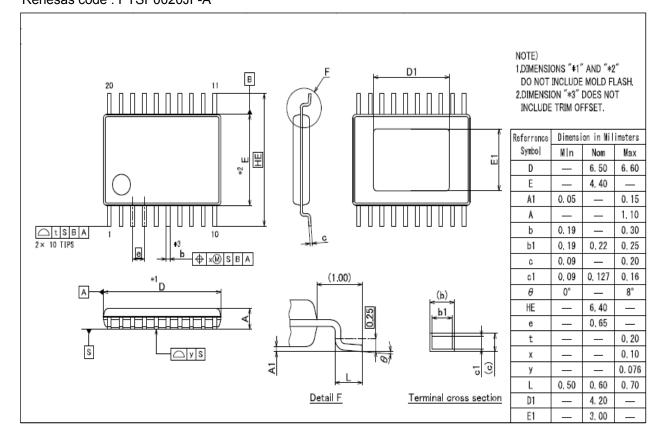
When EN pin and x\_AutoPFM pin are fixed, connect to a pin listed below.

Input Pin	Connect Pin			
input Fin	Fixed to Low Level	Fixed to High Level		
EN1	GND	VIN		
EN2	GND	VIN		
x_AutoPFM	GND	VIN		



## Package Dimensions

#### 20pin HTSSOP Renesas code : PTSP0020JF-A





**Revision History** 

# RAA23022x, RAA23023x Preliminary Datasheet

		Description		
Rev.	Date	Page	Summary	
0.00	Aug.19. 2014	-	First Edition issued	

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